WHAT IS CLAIMED IS:

1. A semiconductor device comprising:

a base substrate provided with a base wiring;

a first substrate that includes a first wiring to be electrically connected to the base wiring, and is provided above the base substrate;

a first semiconductor element that is provided between the base substrate and the first substrate;

a second substrate that includes a second wiring to be electrically connected to the base wiring, and is provided above the first substrate; and

a second semiconductor element that is provided between the first substrate and the second substrate and above the first semiconductor element,

wherein the first substrate has a first region where the first semiconductor element is provided below, a second region where a portion of the first wiring that connects to the base wiring is located, and a first bent section between the first region and the second region, and

the second substrate has a third region where the second semiconductor element is provided below, a fourth region where a portion of the second wiring that connects to the base wiring is located, and a second bent section between the third region and the fourth region.

2. The semiconductor device according to claim 1, further comprising:

a first electrode that is provided on the first semiconductor element; and

a second electrode that is provided on the second semiconductor element,

wherein the first electrode is electrically connected to the first wiring, and

the second electrode is electrically connected to the second wiring.

3. The semiconductor device according to claim 2, further comprising:

a surface of the first semiconductor element that includes the first electrode has a rectangular shape including a first side and a second side that is longer than the first side and intersects the first side; and

a surface of the second semiconductor element that includes the second electrode has a rectangular shape including a third side and a fourth side that is longer than the third side and intersects the third side,

wherein the first semiconductor element and the second semiconductor element are disposed such that the second side and the fourth side are in parallel with each other.

4. The semiconductor device according to claim 2, further comprising:

a surface of the first semiconductor element that includes the first electrode has a rectangular shape including a first side and a second side that is longer than the first side and intersects the first side; and

a surface of the second semiconductor element that includes the second electrode has a rectangular shape including a third side and a fourth side that is longer than the third side and intersects the third side,

wherein the first semiconductor element and the second semiconductor element are disposed such that the second side and the fourth side projected onto the base substrate intersect each other.

5. The semiconductor device according to claim 1, further comprising:

a surface of the first substrate that opposes a surface of the base substrate has a rectangular shape including a first side and a second side that is longer than the first side and intersects the first side, and

a surface of the second substrate that opposes a surface of the base substrate has a rectangular shape including a third side and a fourth side that is longer than the third side and intersects the third side,

wherein the first substrate and the second substrate are disposed such that the second side and the fourth side are in parallel with each other.

6. The semiconductor device according to claim 1, further comprising:

a surface of the first substrate that opposes a surface of the base substrate has a rectangular shape including a first side and a second side that is longer than the first side and intersects the first side; and

a surface of the second substrate that opposes a surface of the base substrate has a rectangular shape including a third side and a fourth side that is longer than the third side and intersects the third side,

wherein the first substrate and the second substrate are disposed such that the second side and the fourth side projected onto the base substrate intersect each other.

7. The semiconductor device according to claim 1, wherein an opening section is formed in the first substrate at the first bent section.

8. The semiconductor device according to claim 1 , wherein an opening section is formed in the second substrate at the second bent section.

9. A method for manufacturing a semiconductor device, comprising:

disposing a first substrate provided with a first wiring above a base substrate provided with a base wiring;

disposing a first semiconductor element between the first substrate and the base substrate;

providing a first bent section in the first substrate and electrically connecting the first wiring to the base wiring;

disposing the second substrate provided with a second wiring above the first substrate;

disposing a second semiconductor element between the first substrate and the second substrate; and

providing a second bent section in the second substrate, and electrically connecting the second wiring to the base wiring.

10. The method for manufacturing a semiconductor device according to claim 9, further comprising;

connecting a first electrode provided on the first semiconductor element to the first wiring; and

connecting a second electrode provided on the second semiconductor element to the second wiring.

11. The method for manufacturing a semiconductor device according to claim 10, further comprising:

providing a surface of the first semiconductor element that includes the first electrode with a rectangular shape including a first side and a second side that is longer than the first side and intersects the first side;

providing a surface of the second semiconductor element that includes the second electrode with a rectangular shape including a third side and a fourth side that is longer than the third side and intersects the third side; and

disposing in the second substrate is disposed such that the second side and the fourth side are in parallel with each other.

12. The method for manufacturing a semiconductor device according to claim 9, further comprising:

providing a surface of the first semiconductor element that includes the first electrode with a rectangular shape including a first side and a second side that is longer than the first side and intersects the first side;

providing a surface of the second semiconductor element that includes the second electrode with a rectangular shape including a third side and a fourth side that is longer than the third side and intersects the third side; and

disposing the second substrate such that the second side and the fourth side projected onto the base substrate intersect each other.

13. The method for manufacturing a semiconductor device according to claim 9, further comprising:

providing a surface of the first substrate that opposes a surface of the base substrate with a rectangular shape including a first side and a second side that is longer than the first side and intersects the first side;

providing a surface of the second substrate that opposes a surface of the base substrate with a rectangular shape including a third side and a fourth side that is longer than the third side and intersects the third side; and

disposing the second substrate such that the second side and the fourth side projected onto the base substrate are in parallel with each other.

14. The method for manufacturing a semiconductor device according to claim 9, further comprising:

providing a surface of the first substrate that opposes a surface of the base substrate with a rectangular shape including a first side and a second side that is longer than the first side and intersects the first side;

providing a surface of the second substrate that opposes a surface of the base substrate with a rectangular shape including a third side and a fourth side that is longer than the third side and intersects the third side; and

disposing the second substrate such that the second side and the fourth side projected onto the base substrate intersect each other.

15. A method for manufacturing a semiconductor device according to claim 9, further comprising:

forming a first opening section in the first substrate before providing the first substrate above the base substrate,

wherein, in providing the first substrate above the base substrate, the first bent section is provided at a section where the first opening section is formed.

16. The method for manufacturing a semiconductor device according to claim 9, further comprising:

forming a second opening section in the second substrate before providing the second substrate above the first substrate,

wherein, in providing the second substrate above the first substrate, the second bent section is provided at a section where the second opening section is formed.

17. An electronic equipment comprising a semiconductor device recited in claim 1.

18. The semiconductor device according to claim 3, wherein an opening section is formed in the first substrate at the first bent section.

19. The semiconductor device according to claim 3 , wherein an opening section is formed in the second substrate at the second bent section.

20. The method for manufacturing a semiconductor device according to claim 11, further comprising:

forming a first opening section in the first substrate before providing the first substrate above the base substrate,

wherein, in providing the first substrate above the base substrate, the first bent section is provided at a section where the first opening section is formed.

21. The method for manufacturing a semiconductor device according to claim 12, further comprising:

forming a first opening section in the first substrate before providing the first substrate above the base substrate,

wherein, in providing the first substrate above the base substrate, the first bent section is provided at a section where the first opening section is formed.

22. The method for manufacturing a semiconductor device according to claim 11, further comprising:

forming a second opening section in the second substrate before providing the second substrate above the first substrate,

wherein, in providing the second substrate above the first substrate, the second bent section is provided at a section where the second opening section is formed.